

BB405M

Build in Biasing Circuit MOS FET IC
UHF/VHF RF Amplifier

HITACHI

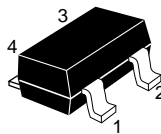
ADE-208-718B (Z)
3rd. Edition
Mar. 2001

Features

- Build in Biasing Circuit; To reduce using parts cost & PC board space.
- Superior cross modulation characteristics.
- High gain;
(PG = 28 dB typ. at f = 200 MHz)
- Wide supply voltage range;
Applicable with 5V to 9V supply voltage.
- Withstanding to ESD;
Build in ESD absorbing diode. Withstand up to 200V at C=200pF, Rs=0 conditions.
- Provide mini mold packages; MPAK-4R(SOT-143 var.)

Outline

MPAK-4R



1. Source
2. Drain
3. Gate2
4. Gate1

- Notes:
1. Marking is "EX -".
 2. BB405M is individual type number of HITACHI BBFET.

Absolute Maximum Ratings (Ta = 25°C)

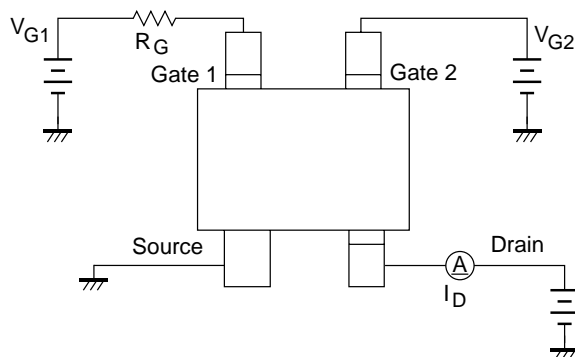
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	12	V
Gate1 to source voltage	V_{G1S}	+10 - 0	V
Gate2 to source voltage	V_{G2S}	±10	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

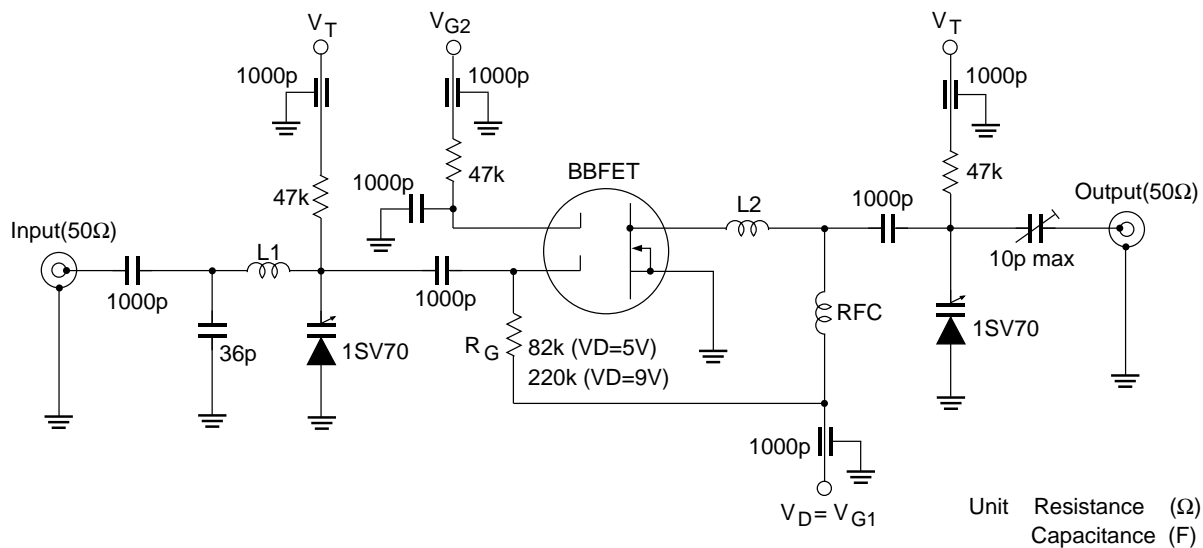
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	12	—	—	V	$I_D = 200\mu A, V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+10	—	—	V	$I_{G1} = +10\mu A, V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	±10	—	—	V	$I_{G2} = \pm 10\mu A, V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +9V, V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I_{G2SS}	—	—	±100	nA	$V_{G2S} = \pm 9V, V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.4	0.7	1.0	V	$V_{DS} = 5V, V_{G2S} = 4V, I_D = 100\mu A$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.4	0.7	1.0	V	$V_{DS} = 5V, V_{G1S} = 5V, I_D = 100\mu A$
Input capacitance	C_{iss}	2.3	2.8	3.5	pF	$V_{DS} = 5V, V_{G1} = 5V$
Output capacitance	C_{oss}	1.1	1.5	1.9	pF	$V_{G2S} = 4V, R_G = 82k\Omega$
Reverse transfer capacitance	C_{fss}	—	0.017	0.04	pF	$f = 1MHz$
Drain current	$I_{D(op)1}$	10	15	20	mA	$V_{DS} = 5V, V_{G1} = 5V$ $V_{G2S} = 4V, R_G = 82k\Omega$
	$I_{D(op)2}$	—	13	—	mA	$V_{DS} = 9V, V_{G1} = 9V$ $V_{G2S} = 6V, R_G = 220k\Omega$
Forward transfer admittance	$ y_{fs} 1$	23	28	—	mS	$V_{DS} = 5V, V_{G1} = 5V, V_{G2S} = 4V$ $R_G = 82k\Omega, f = 1kHz$
	$ y_{fs} 2$	—	28	—	mS	$V_{DS} = 9V, V_{G1} = 9V, V_{G2S} = 6V$ $R_G = 220k\Omega, f = 1kHz$
Power gain	PG1	24	28	—	dB	$V_{DS} = 5V, V_{G1} = 5V, V_{G2S} = 4V$ $R_G = 82k\Omega, f = 200MHz$
	PG2	—	28	—	dB	$V_{DS} = 9V, V_{G1} = 9V, V_{G2S} = 6V$ $R_G = 220k\Omega, f = 200MHz$
Noise figure	NF1	—	1.4	1.9	dB	$V_{DS} = 5V, V_{G1} = 5V, V_{G2S} = 4V$ $R_G = 82k\Omega, f = 200MHz$
	NF2	—	1.4	—	dB	$V_{DS} = 9V, V_{G1} = 9V, V_{G2S} = 6V$ $R_G = 220k\Omega, f = 200MHz$

Main Characteristics

Test Circuit for Operating Items ($I_{D(op)}$, $|y_{fs}|$, C_{iss} , C_{oss} , C_{rss} , NF, PG)

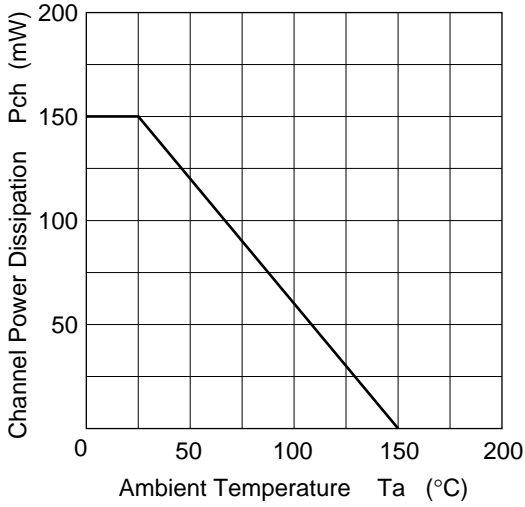


200MHz Power Gain, Noise Figure Test Circuit

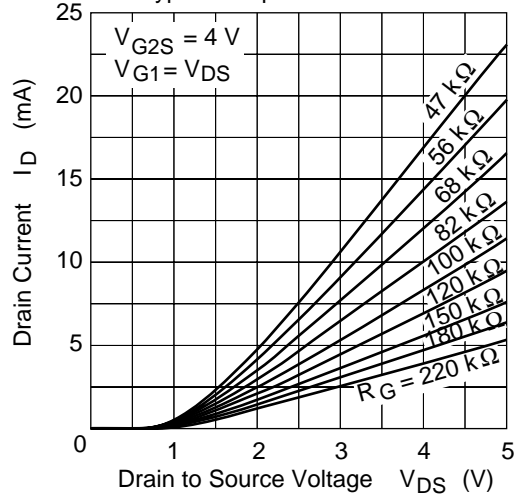


- L1 : ϕ 1mm Enameled Copper Wire, Inside dia 10mm, 2Turns
- L2 : ϕ 1mm Enameled Copper Wire, Inside dia 10mm, 2Turns
- RFC : ϕ 1mm Enameled Copper Wire, Inside dia 5mm, 2Turns

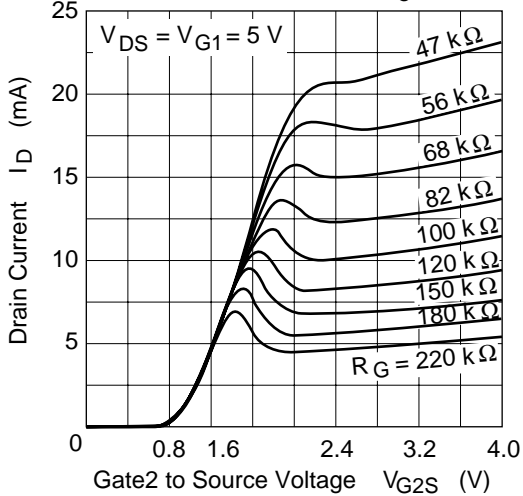
Maximum Channel Power Dissipation Curve



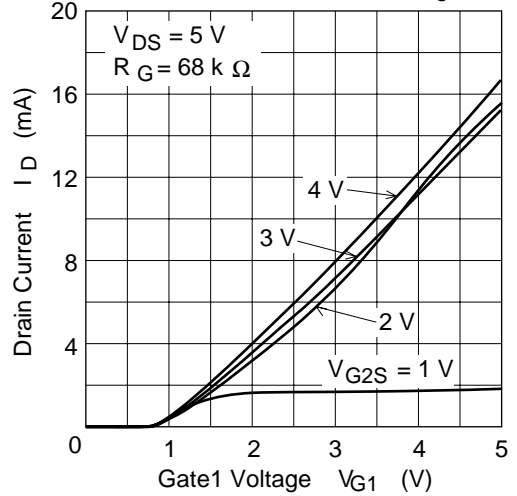
Typical Output Characteristics

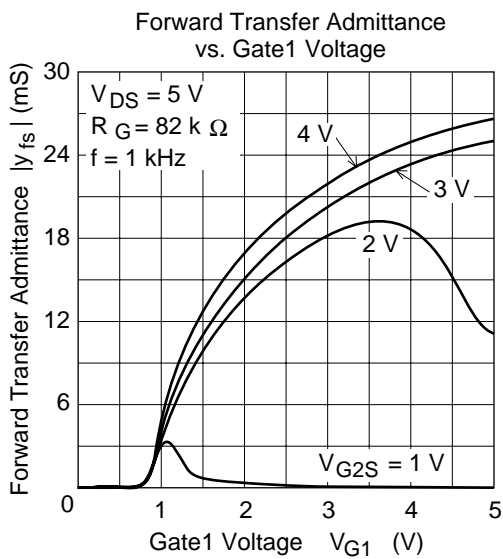
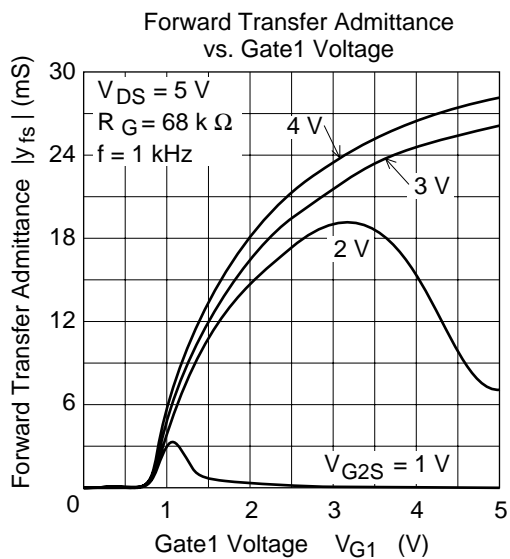
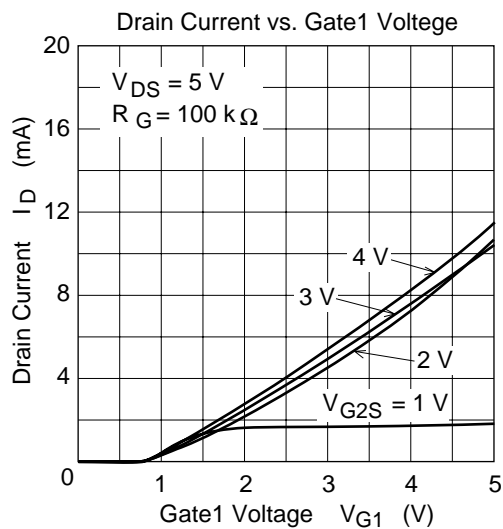
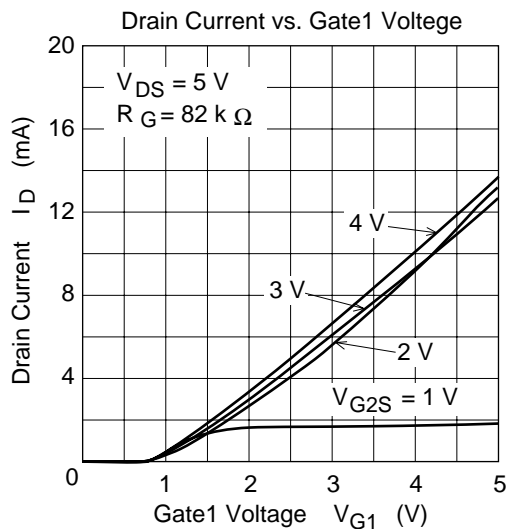


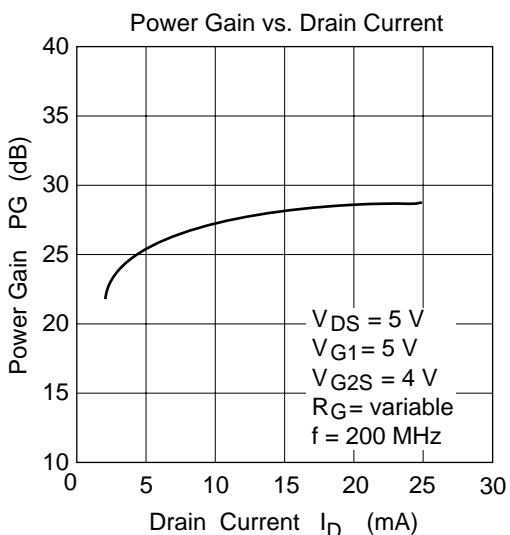
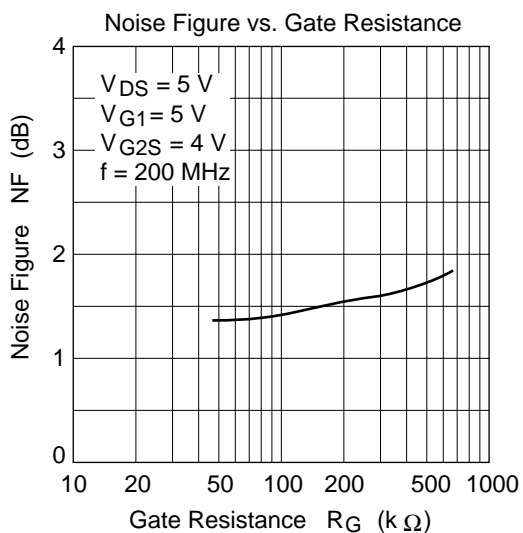
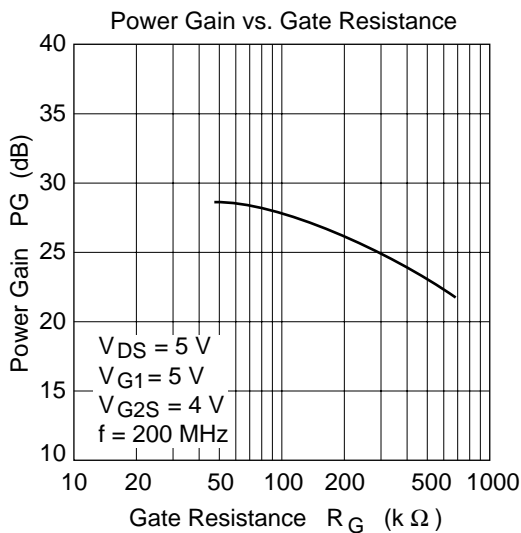
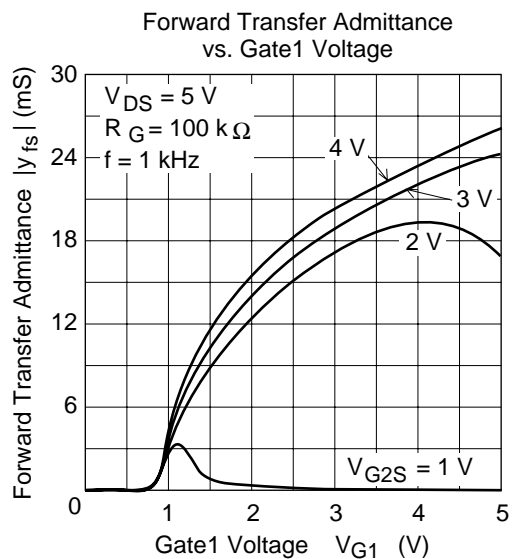
Drain Current vs. Gate2 to Source Voltage



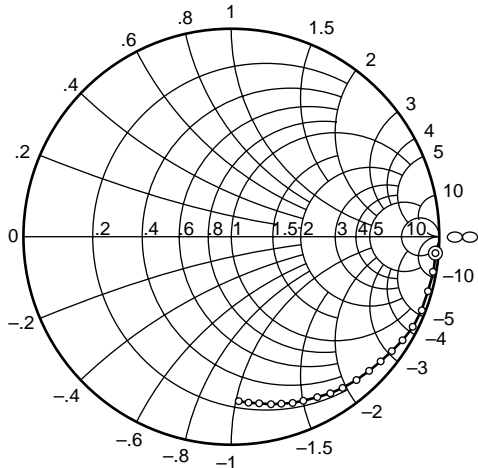
Drain Current vs. Gate1 Voltage







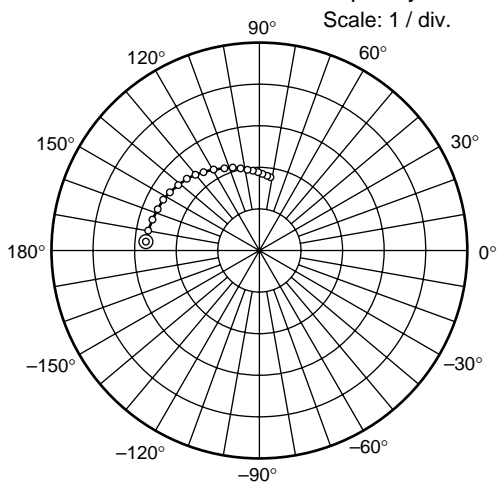
S11 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 82\text{ k}\Omega$
 50 to 1000 MHz (50 MHz step)

⊙—○

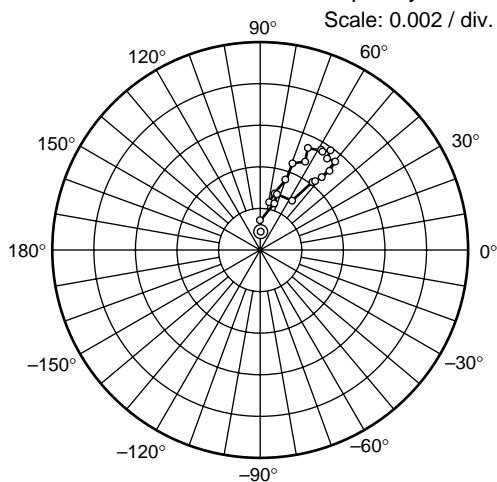
S21 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 82\text{ k}\Omega$
 50 to 1000 MHz (50 MHz step)

⊙—○

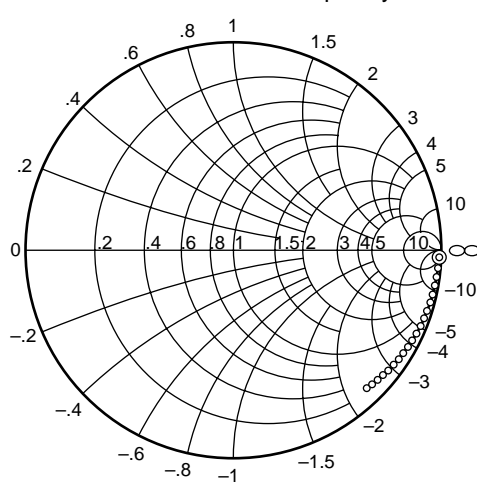
S12 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 82\text{ k}\Omega$
 50 to 1000 MHz (50 MHz step)

⊙—○

S22 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 82\text{ k}\Omega$
 50 to 1000 MHz (50 MHz step)

⊙—○

BB405M

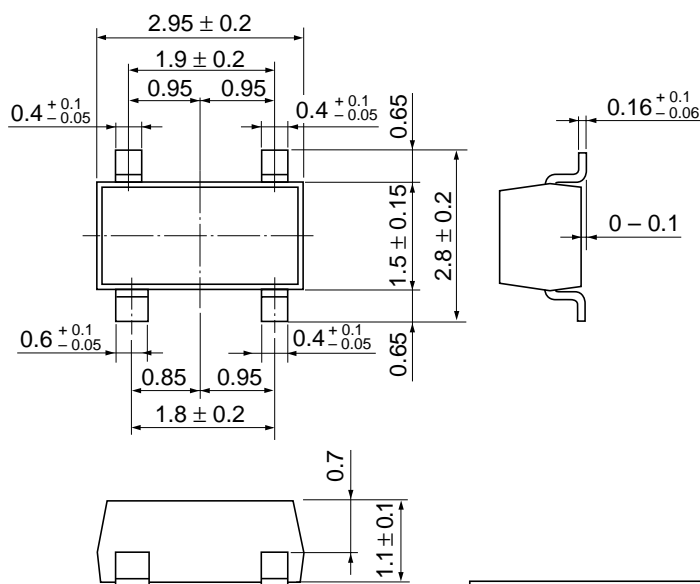
Sparameter ($V_{DS} = V_{G1} = 5V$, $V_{G2S} = 4V$, $R_G = 82k\Omega$, $Z_O = 50\Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
50	0.991	-4.8	2.69	174.9	0.00090	91.4	0.991	-2.2
100	0.991	-9.9	2.68	169.3	0.00153	90.5	0.992	-4.8
150	0.982	-15.4	2.66	163.4	0.00243	73.8	0.991	-7.5
200	0.975	-20.7	2.62	157.5	0.00293	74.9	0.989	-9.9
250	0.972	-25.6	2.60	152.0	0.00370	70.1	0.985	-12.6
300	0.956	-30.6	2.54	146.3	0.00444	69.0	0.981	-15.0
350	0.942	-35.5	2.47	140.9	0.00478	63.7	0.977	-17.3
400	0.928	-40.1	2.42	135.7	0.00535	64.8	0.973	-19.7
450	0.920	-44.9	2.38	130.5	0.00551	56.8	0.967	-22.0
500	0.906	-49.2	2.32	125.7	0.00549	58.6	0.962	-24.5
550	0.894	-53.6	2.25	120.8	0.00584	54.4	0.957	-26.9
600	0.880	-57.8	2.18	116.2	0.00542	53.3	0.952	-29.2
650	0.868	-62.1	2.12	111.5	0.00562	49.5	0.944	-31.5
700	0.854	-66.2	2.06	106.8	0.00509	48.6	0.939	-33.8
750	0.842	-70.3	2.00	102.5	0.00465	49.7	0.933	-36.1
800	0.835	-73.9	1.94	98.4	0.00427	51.6	0.927	-38.3
850	0.820	-77.7	1.89	94.0	0.00416	53.3	0.921	-40.5
900	0.802	-81.5	1.83	89.6	0.00289	57.9	0.915	-42.7
950	0.801	-84.7	1.78	85.6	0.00288	72.9	0.909	-44.9
1000	0.789	-87.9	1.73	82.1	0.00241	78.9	0.904	-47.1

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	MPAK-4R
JEDEC	—
EIAJ	—
Mass (reference value)	0.013 g

Cautions

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
	Japan	: http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher StraÙe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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